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### **STTH1002C-Y**

### Automotive high efficiency ultrafast diode

#### **Features**

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- High junction temperature
- Low leakage current
- AEC-Q101 qualified

### **Description**

Dual center tap rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in DPAK and D<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection for automotive applications.

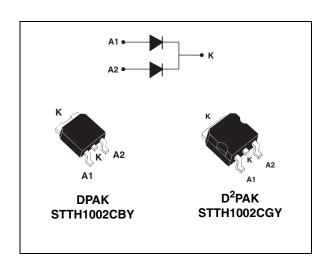


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	Up to 2 x 8 A
$V_{RRM}$	200 V
T <sub>j</sub> (max)	175 °C
V <sub>F</sub> (typ)	0.78 V
t <sub>rr</sub> (typ)	20 ns

Characteristics STTH1002C-Y

### 1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit			
$V_{RRM}$	Repetitive peak reverse voltage			200	V	
1	D <sup>2</sup> PAK				Δ.	
'F(RMS)	I <sub>F(RMS)</sub> Forward rms current		DPAK	10	Α	
		T <sub>c</sub> = 155 °C	Per diode	5		
,	Average forward current S OF	T <sub>c</sub> = 150 °C	Per device	10	Α	
I <sub>F(AV)</sub>	Avarage forward current $\delta = 0.5$	T <sub>c</sub> = 135 °C	Per diode	8	A	
		T <sub>c</sub> = 125 °C	Per device	16		
I <sub>FSM</sub>	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			50	Α	
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C	
Tj	Operating junction temperature range			-40 to + 175	°C	

Table 3. Thermal parameters

Symbol	Parameter	Value (max)	Unit
D	Junction to case Per diode	4.0	
R <sub>th(j-c)</sub>	Per device	2.5	°C/W
R <sub>th(j-c)</sub>	Coupling	1.0	

When the diodes 1 and 2 are used simultaneously:  $\Delta T_i$  (diode1) = P(diode1) x  $R_{th(i-c)}$  (per diode) + P(diode2) x  $R_{th(c)}$ 

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V- <b>-</b> V			5	μA
'R''	neverse leakage current	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$		3	40	μΑ
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 5 A			1.1	
V (2)		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 10 A			1.25	V
VF` ′		T <sub>j</sub> = 150 °C	I <sub>F</sub> = 5 A		0.78	0.89	V
		T <sub>j</sub> = 150 °C	I <sub>F</sub> = 10 A			1.05	

<sup>1.</sup> Pulse test:  $t_p$  = 5 ms,  $\delta$  < 2 %

To evaluate the conduction losses use the following equation:

$$P = 0.73 \times I_{F(AV)} + 0.032 I_{F}^{2}_{(RMS)}$$

<sup>2.</sup> Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2 %

STTH1002C-Y Characteristics

Table 5. Dynamic electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
t <sub>rr</sub>	,	,	$I_F = 1 \text{ A V}_R = 30 \text{ V}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		20	25	ns
I <sub>RM</sub>	Reverse recovery current	T <sub>j</sub> = 125 °C	$I_F = 5 \text{ A}$ $V_R = 160 \text{ V}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$		5.9	7.6	Α
t <sub>fr</sub>	Forward recovery time	T <sub>j</sub> = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$			110	ns
V <sub>FP</sub>	Forward recovery voltage	T <sub>j</sub> = 25 °C	$I_F = 5 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		2.4		V

Characteristics STTH1002C-Y

Figure 1. Peak current versus duty cycle (per diode)

1M(A)
60
40
40
40
40
P = 10W
8
6=tp/T + tp

Figure 2. Forward voltage drop versus forward current (typical values, per diode)

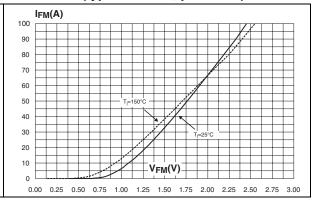


Figure 3. Forward voltage drop versus forward current (maximum values, per diode)

0.3 0.4 0.5 0.6

0.1

0.0

| IFM(A) | 100 | 80 | 70 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100 | 100

Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

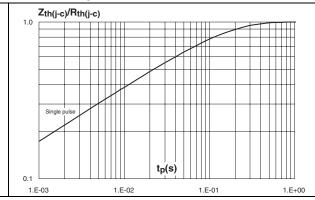
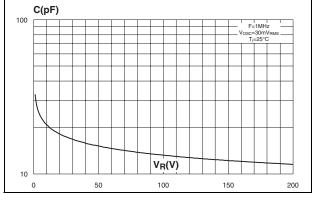
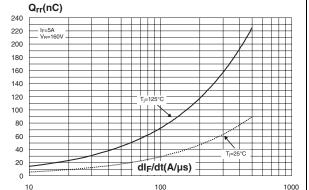


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

Figure 6. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values, per diode)





STTH1002C-Y Characteristics

Figure 7. Reverse recovery time versus dl<sub>F</sub>/dt Figure 8. (typical values, per diode)

### Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values, per diode)

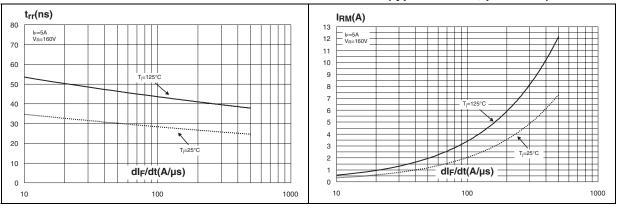


Figure 9. Dynamic parameters versus junction temperature

Figure 10. Thermal resistance junction to ambient versus copper surface under tab for D<sup>2</sup>PAK

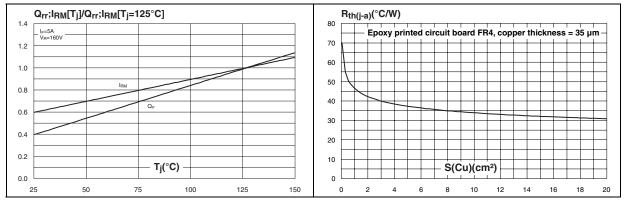
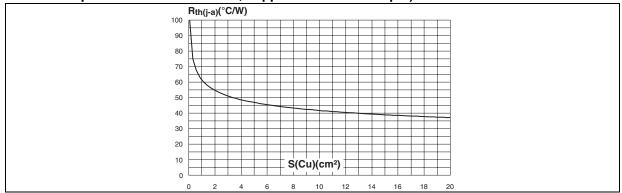


Figure 11. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness = 35 µm) for DPAK

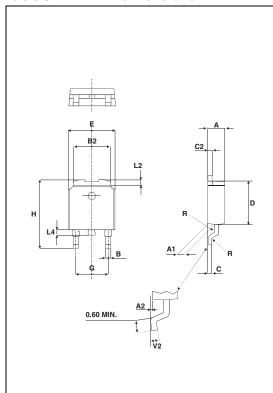


### 2 Package mechanical data

- Epoxy meets UL94, V0
- Cooling method: by conduction (method C)

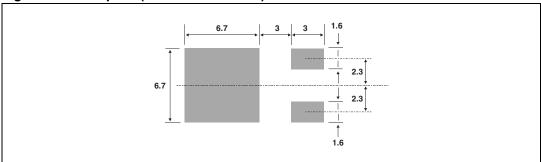
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Table 6. DPAK dimensions



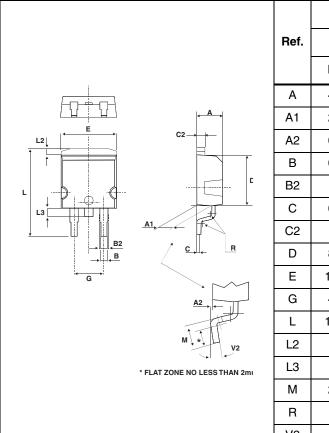
	Dimensions					
Ref.	Millim	neters	Inc	hes		
	Min.	Max.	Min.	Max.		
Α	2.20	2.40	0.086	0.094		
A1	0.90	1.10	0.035	0.043		
A2	0.03	0.23	0.001	0.009		
В	0.64	0.90	0.025	0.035		
B2	5.20	5.40	0.204	0.212		
С	0.45	0.60	0.017	0.023		
C2	0.48	0.60	0.018	0.023		
D	6.00	6.20	0.236	0.244		
Е	6.40	6.60	0.251	0.259		
G	4.40	4.60	0.173	0.181		
Н	9.35	10.10	0.368	0.397		
L2	0.80 typ.		0.03	1 typ.		
L4	0.60	1.00	0.023	0.039		
V2	0°	8°	0°	8°		

Figure 12. Footprint (dimensions in mm)



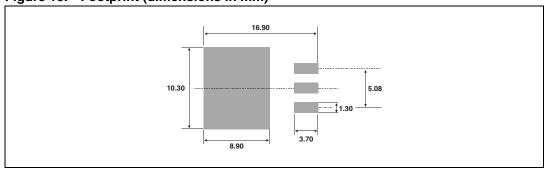
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Table 7. D<sup>2</sup>PAK dimensions



	Dimensions				
Ref.	Millim	neters	Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.40	1.75	0.055	0.069	
М	2.40	3.20	0.094	0.126	
R	0.40	typ.	0.016	6 typ.	
V2	0°	8°	0°	8°	

Figure 13. Footprint (dimensions in mm)



Ordering information STTH1002C-Y

# 3 Ordering information

Table 8. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode	
STTH1002CBY-TR	STTH1002CY	DPAK	0.3 g	2500	Tane and real	
STTH1002CGY-TR	STTH1002CGY	D <sup>2</sup> PAK	1.48 g	1000	- Tape and reel	

## 4 Revision history

Table 9. Document revision history

Date	Revision	Changes
21-Oct-2010	1	First issue.
03-Nov-2011	2	Updated Table 7 and Table 8.

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